a first silicon nitride layer provided by a CVD method on said silicon oxide layer; and

a second silicon nitride layer provided by a JVD method on said first silicon nitride layer and having a lower trap density than that of said first silicon nitride layer.

C1

Rewrite claim 2 as follows:

2. A non volatile semiconductor memory device according to claim 1, wherein said JVD method is performed by carrying, over a surface of said substrate, active Si and N obtained by plasma-decomposing at least a silane series gas and a gas containing nitrogen.

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Rewrite claim 5 as follows:

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C2

5. A non-volatile semiconductor memory device comprising:

a semiconductor substrate; and

a memory cell having a floating gate provided through a tunnel insulating layer on said semiconductor substrate, and a control gate provided through an inter-layer insulating layer on said floating gate,

wherein said inter-layer insulating layer includes:

a silicon oxide layer contiguous to said floating gate; and

a silicon nitride layer deposited by a JVD method on said silicon oxide layer and having a lower trap density than an ordinary trap density obtained by a typical CVD condition.

Rewrite claim 6 as follows:

6. A non-volatile semiconductor memory device according to claim 5, wherein said JVD method is performed by carrying, over a surface of said substrate, active Si and N obtained by plasma-decomposing at least a silane-series gas and a gas containing nitrogen.

Rewrite claim 7 as follows:

7. A non-volatile semiconductor memory device comprising:

a semiconductor substrate; and

a memory cell having a floating gate provided through a tunnel insulating layer on said semiconductor substrate, and a control gate provided through an inter-layer insulating layer on said floating gate,

wherein said inter-layer insulating layer includes:

a silicon oxide layer contiguous to said floating gate; and

a silicon nitride layer deposited by a JVD method on said silicon oxide layer and having a quantity of hydrogen content on the order of $10^{19}/cm^3$ or less.

Rewrite claim 8 as follows:

8. A non-volatile semiconductor memory device according to claim 7, wherein said JVD method is performed by carrying, over a surface of said substrate, active Si and N obtained by plasma-decomposing at least a silane series gas and a gas containing nitrogen.

Rewrite claim 9 as follows:

9. A non-volatile semiconductor memory device comprising:

a semiconductor substrate; and

a memory cell having a floating gate provided through a tunnel insulating layer on said semiconductor substrate, and a control gate provided through an inter-layer insulating layer on said floating gate,

wherein said inter-layer insulating layer includes:

a silicon nitride layer deposited by a JVD method, serving as a layer contiguous to at least one of said floating gate and said control gate, and having a lower trap density than an ordinary trap density obtained by a typical CVD condition.

Rewrite claim 10 as follows:

10. A non-volatile semiconductor memory device according to claim 9, wherein said JVD method is performed by carrying, over a surface of said substrate,

active Si and N obtained by plasma-decomposing at least a silane-series gas and a gas containing nitrogen.

Rewrite claim 14 as follow:

14. A non-volatile semiconductor memory device comprising:

a semiconductor substrate; and

a memory cell having a floating gate provided through a tunnel insulating layer on said semiconductor substrate, and a control gate provided through an inter-layer insulating layer on said floating gate,

wherein said inter-layer insulating layer includes:

a silicon nitride layer serving as a layer contiguous to at least one of said floating gate and said control gate, and having a quantity of hydrogen content on the order of $10^{19}/cm^3$ or less.

Rewrite claim 15 as follows:

15. A non-volatile semiconductor memory device according to claim 14, wherein said JVD method is performed by carrying, over a surface of said substrate, active Si and N obtained by plasma-decomposing at least a silane-series gas and a gas containing nitrogen

## REMARKS

Claims 1-18 are pending in the application. By this amendment, claims 1, 2, 5, 6, 7, 8, 9, 10, 14 and 15 are being amended to advance the prosecution of the